



# 1 Megabit Serial Flash

## SST45LF010

Data Sheet

### FEATURES:

- **Single 3.0-3.6V Read and Write Operations**
- **Serial Interface Architecture**
- **Byte Serial Read with Single Command**
- **Superior Reliability**
  - Endurance: 100,000 Cycles (typical)
  - Greater than 100 years Data Retention
- **Low Power Consumption**
  - Active Current: 10 mA (typical)
  - Standby Current: 10  $\mu$ A (typical)
- **Sector or Chip-Erase Capability**
  - Uniform 4 KByte sectors
- **Fast Erase and Byte-Program**
  - Chip-Erase Time: 70 ms (typical)
  - Sector-Erase Time: 18 ms (typical)
  - Byte-Program Time: 14  $\mu$ s (typical)
- **Automatic Write Timing**
  - Internal  $V_{PP}$  Generation
- **End-of-Write Detection**
  - Software Status
- **10 MHz Max Clock Frequency**
- **Hardware Reset Pin (RST#)**
  - Resets the device to Standby Mode
- **CMOS I/O Compatibility**
- **Hardware Data Protection (WP#)**
  - Protects and unprotects the device from Write operation
- **Packages Available**
  - 8-lead SOIC (4.9mm x 6mm)
  - 8-contact WSON

### PRODUCT DESCRIPTION

The SST45LF010 is a 1 Mbit serial flash memory manufactured with SST's proprietary, high performance CMOS SuperFlash technology. The 1 Mbit of memory is organized as 32 sectors of 4096 Bytes. The flash memory uses a 3-wire serial interface and a chip enable to select and sequentially access its data. The serial interface consists of; serial data input (SI), serial data output (SO), serial clock (SCK), and chip enable (CE#). A write protect (WP#) inhibits the entire memory from write operation and a hardware reset pin (RST#) resets the device to standby mode.

The SST45LF010 device is offered in both 8-lead SOIC and 8-contact WSON packages. See Figure 1 for the pinouts.

#### Device Operation

The SST45LF010 uses bus cycles of 8 bits each for commands, data, and addresses to execute operations. The operation instructions are listed in Table 3.

All instructions are synchronized off a high to low transition of CE#. The first low to high transition on SCK will initiate the instruction sequence. Inputs will be accepted on the rising edge of SCK starting with the most significant bit. Any low to high transition on CE# before the input instruction completes will terminate any instruction in progress and return the device to the standby mode.

#### Read

The Read operation outputs the data in order from the initial accessed address. While SCK is input, the address will be incremented automatically until end (top) of the address space (1FFFFH), then the internal address pointer automatically increments to beginning (bottom) of the address space (00000H), and data out stream will continue. The read data stream is continuous through all addresses until terminated by a low to high transition on CE#.

#### Sector/Chip-Erase Operation

The Sector-Erase operation clears all bits in the selected sector to FFH. The Chip-Erase instruction clears all bits in the device to FFH.

#### Byte-Program Operation

The Byte-Program operation programs the bits in the selected byte to the desired data. The selected byte must be in the erased state (FFH) when initiating a Program operation. The data is input from bit 7 to bit 0 in order.

#### Software Status Operation

The Status operation determines if an Erase or Program operation is in progress. If bit 0 is at a "0" an Erase or Program operation is in progress, the device is busy. If bit 0 is at a "1" the device is ready for any valid operation. The status read is continuous with ongoing clock cycles until terminated by a low to high transition on CE#.





## Reset

Reset will terminate any operation, e.g., Read, Erase and Program, in progress. It is activated by a high to low transition on the RST# pin. The device will remain in reset condition as long as RST# is low. Minimum reset time is 10  $\mu$ s. See Figure 14 for reset timing diagram. RST# is internally pulled-up and could remain unconnected during normal operation. After reset, the device is in standby mode, a high to low transition on CE# is required to start the next operation.

An internal power-on reset circuit protects against accidental data writes. Applying a logic level low to RST# during the power-on process then changing to a logic level high when V<sub>DD</sub> has reached the correct voltage level will provide additional protection against accidental writes during power on.

## Read SST ID/Read Device ID

The Read SST ID and Read Device ID operations read the JEDEC assigned manufacturer identification and the manufacturer assigned device identification IDs. These IDs may be used to determine the actual device resident in the system.

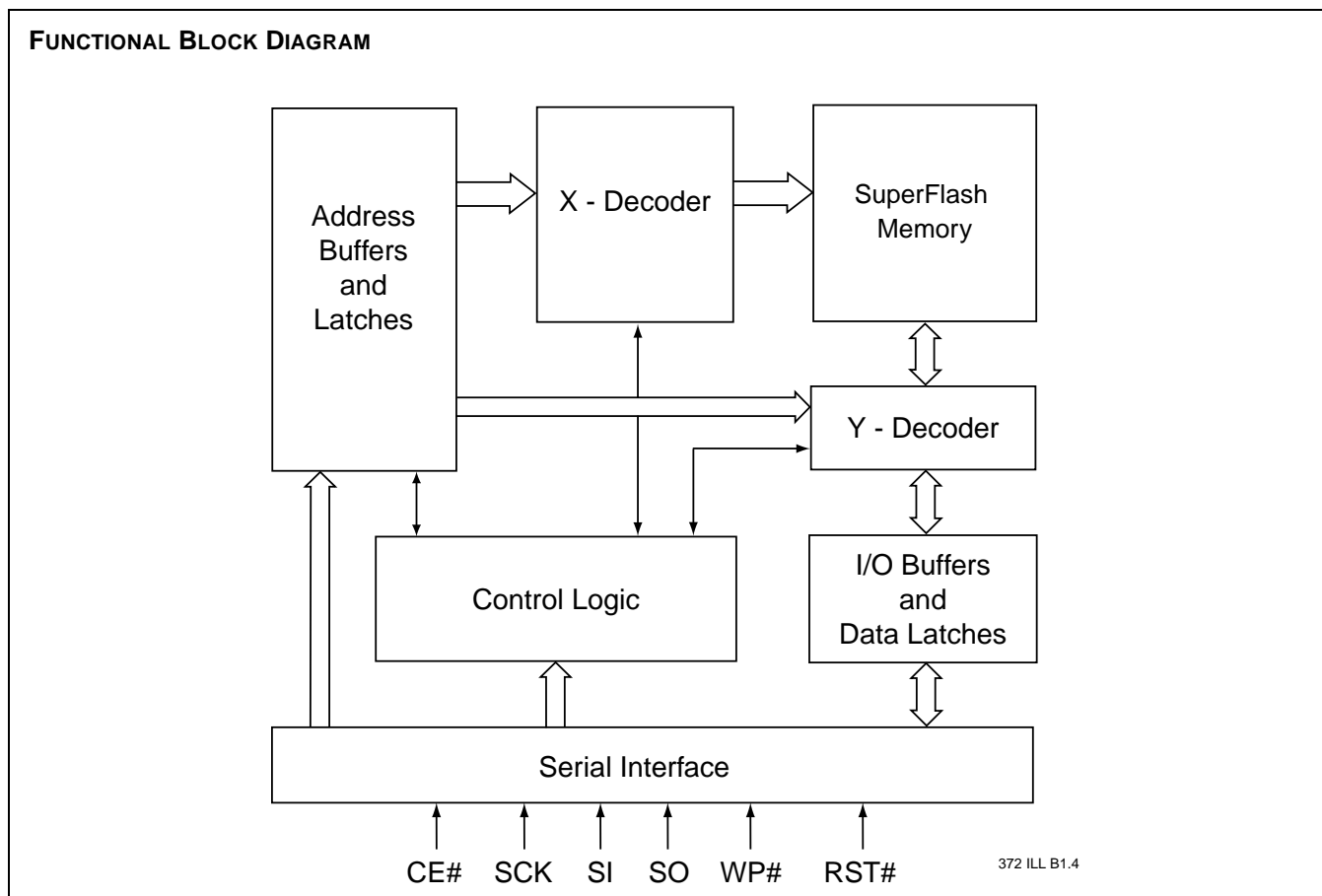
**TABLE 1: PRODUCT IDENTIFICATION**

	Byte	Data
Manufacturer's ID	0000H	BFH
Device ID	0001H	42H

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## Write Protect

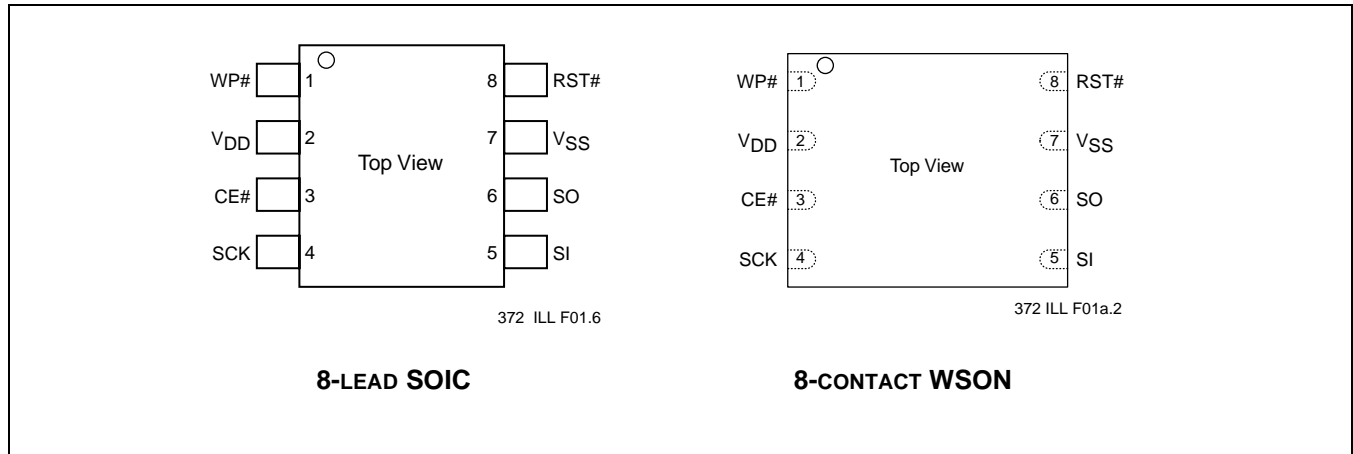
The WP# pin provides inadvertent write protection. The WP# pin must be held high for any Erase or Program operation. The WP# pin is "Don't Care" for all other operations. In typical use, the WP# pin is connected to V<sub>SS</sub> with a standard pull-down resistor. WP# is then driven high whenever an Erase or Program operation is required. If the WP# pin is tied to V<sub>DD</sub> with a pull-up resistor, then all operations may occur and the write protection feature is disabled. The WP# pin has an internal pull-up and could remain unconnected when not used.





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**FIGURE 1: PIN ASSIGNMENTS**

**TABLE 2: PIN DESCRIPTION**

Symbol	Pin Name	Functions
SCK	Serial Clock	To provide the timing of the serial interface. Commands, addresses, or input data are latched on the rising edge of the clock input, while output data is shifted out on the falling edge of the clock input.
SI	Serial Data Input	To transfer commands, addresses, or data serially into the device. Inputs are latched on the rising edge of the serial clock.
SO	Serial Data Output	To transfer data serially out of the device. Data is shifted out on the falling edge of the serial clock.
CE#	Chip Enable	The device is enabled by a high to low transition on CE#.
WP#	Write Protect	To protect the device from unintentional Write (Erase or Program) operations. When WP# is low, all Erase and Program commands are ignored. When WP# is high, the device may be erased or programmed. This pin has an internal pull-up and could remain unconnected when not used.
RST#	Reset	A high to low transition on RST# will terminate any operation in progress and reset the internal logic to the standby mode. The device will remain in the reset condition as long as the RST# is low. Operations may only occur when RST# is high. This pin has an internal pull-up and could remain unconnected when not used.
V <sub>DD</sub>	Power Supply	To provide power supply (3.0-3.6V).
V <sub>SS</sub>	Ground	



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**TABLE 3: DEVICE OPERATION INSTRUCTIONS<sup>1</sup>**

Bus Cycle <sup>2</sup>	1		2		3		4		5		6		7	
Cycle Type/ Operation <sup>3,4</sup>	S <sub>IN</sub>	S <sub>OUT</sub>	S <sub>IN</sub>	S <sub>OUT</sub>	S <sub>IN</sub>	S <sub>OUT</sub>	S <sub>IN</sub>	S <sub>OUT</sub>	S <sub>IN</sub>	S <sub>OUT</sub>	S <sub>IN</sub>	S <sub>OUT</sub>	S <sub>IN</sub>	S <sub>OUT</sub>
Read	FFH	Hi-Z	A <sub>23</sub> -A <sub>16</sub>	Hi-Z	A <sub>15</sub> -A <sub>8</sub>	Hi-Z	A <sub>7</sub> -A <sub>0</sub>	Hi-Z	X	Hi-Z	X	Hi-Z	X	D <sub>OUT</sub>
Sector-Erase <sup>5</sup>	20H	Hi-Z	A <sub>23</sub> -A <sub>16</sub>	Hi-Z	A <sub>15</sub> -A <sub>8</sub>	Hi-Z	X	Hi-Z	D <sub>0H</sub>	Hi-Z	X	Hi-Z	X	Hi-Z
Chip-Erase	60H	Hi-Z	X	Hi-Z	X	Hi-Z	X	Hi-Z	D <sub>0H</sub>	Hi-Z	X	Hi-Z	X	Hi-Z
Byte-Program	10H	Hi-Z	A <sub>23</sub> -A <sub>16</sub>	Hi-Z	A <sub>15</sub> -A <sub>8</sub>	Hi-Z	A <sub>7</sub> -A <sub>0</sub>	Hi-Z	D <sub>IN</sub>	Hi-Z	X	Hi-Z	X	Hi-Z
Status Reg.	9FH	X	X	D <sub>OUT</sub>	X	Note <sup>6</sup>	X	Note <sup>6</sup>	X	Note <sup>6</sup>	X	Note <sup>6</sup>	X	Note <sup>6</sup>
Read-ID	90H	Hi-Z	00H	Hi-Z	00H	Hi-Z	ID Addr <sup>7</sup>	Hi-Z	X	D <sub>OUT</sub> <sup>7</sup>	X	Note <sup>8</sup>	X	Note <sup>8</sup>

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1. For SST45LF010, A<sub>23</sub>-A<sub>17</sub> are "Don't Care."
2. One bus cycle is eight clock periods
3. Operation: S<sub>IN</sub>=Serial In, S<sub>OUT</sub>=Serial Out
4. X=Dummy cycles (Don't Care)
5. A<sub>16</sub>-A<sub>12</sub> are used to determine sector address, A<sub>11</sub>-A<sub>8</sub> are "Don't Care."
6. The status read is continuous with ongoing clock cycles until terminated by a low to high transition on CE#.
7. Manufacturer's ID=BFH, is read with A<sub>0</sub>=0 and Device ID = 42H, is read with A<sub>0</sub>=1; All other address bits are 0
8. The data output is arbitrary.

**TABLE 4: DEVICE OPERATION TABLE**

Operation	SI	SO	CE# <sup>1</sup>	WP#	RST#
Read	X	D <sub>OUT</sub>	Low	X	High
Sector-Erase	X	X	Low	High	High
Chip-Erase	X	X	Low	High	High
Byte-Program	D <sub>IN</sub>	X	Low	High	High
Software-Status	X	D <sub>OUT</sub>	Low	X	High
Reset <sup>2</sup>	X	X	X	X	Low
Read SST ID	X	D <sub>OUT</sub>	Low	X	High
Read Device ID	X	D <sub>OUT</sub>	Low	X	High

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1. A high to low transition on CE# will be required to start any device operation except for Reset.
2. The RST# low will return the device to standby and terminate any Erase or Program operation in progress.



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**Absolute Maximum Stress Ratings** (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
D. C. Voltage on Any Pin to Ground Potential	-0.5V to $V_{DD}+0.5V$
Transient Voltage (<20 ns) on Any Pin to Ground Potential	-1.0V to $V_{DD}+1.0V$
Package Power Dissipation Capability ( $T_a = 25^\circ\text{C}$ )	1.0W
Surface Mount Lead Soldering Temperature (3 Seconds)	240°C
Output Short Circuit Current <sup>1</sup>	50 mA

1. Outputs shorted for no more than one second. No more than one output shorted at a time.

#### OPERATING RANGE

Range	Ambient Temp	$V_{DD}$
Commercial	0°C to +70°C	3.3V±0.3V

#### AC CONDITIONS OF TEST

Input Rise/Fall Time	5 ns
Output Load	$C_L = 30 \text{ pF}$
See Figures 2 and 3	

**TABLE 5: DC OPERATING CHARACTERISTICS  $V_{DD} = 3.0\text{-}3.6\text{V}$**

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
$I_{DD}$	Power Supply Current				f=10 MHz
	Read		20	mA	$CE\#=V_{IL}, V_{DD}=V_{DD} \text{ Max}$
	Program and Erase		30	mA	$CE\#=V_{IL}, V_{DD}=V_{DD} \text{ Max}$
$I_{SB}$	Standby Current		15	$\mu\text{A}$	$CE\#=V_{IHC}, V_{DD}=V_{DD} \text{ Max}$
$I_{LI}$	Input Leakage Current		1	$\mu\text{A}$	$V_{IN}=\text{GND to } V_{DD}, V_{DD}=V_{DD} \text{ Max}$
$I_{LO}$	Output Leakage Current		1	$\mu\text{A}$	$V_{OUT}=\text{GND to } V_{DD}, V_{DD}=V_{DD} \text{ Max}$
$I_{IL}$	Input Low Current <sup>1</sup>		360	$\mu\text{A}$	WP#, RST#=GND
$V_{IL}$	Input Low Voltage		0.8	V	$V_{DD}=V_{DD} \text{ Min}$
$V_{IH}$	Input High Voltage	$0.7 V_{DD}$		V	$V_{DD}=V_{DD} \text{ Max}$
$V_{IHC}$	Input High Voltage (CMOS)	$V_{DD}-0.3$		V	$V_{DD}=V_{DD} \text{ Max}$
$V_{OL}$	Output Low Voltage		0.2	V	$I_{OL}=100 \mu\text{A}, V_{DD}=V_{DD} \text{ Min}$
$V_{OH}$	Output High Voltage	$V_{DD}-0.2$		V	$I_{OH}=-100 \mu\text{A}, V_{DD}=V_{DD} \text{ Min}$

1. This parameter only applies to WP# and RST# pins.



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**TABLE 6: CAPACITANCE (Ta = 25°C, f=1 Mhz, other pins open)**

Parameter	Description	Test Condition	Maximum
C <sub>OUT</sub> <sup>1</sup>	Output Pin Capacitance	V <sub>OUT</sub> = 0V	12 pF
C <sub>IN</sub> <sup>1</sup>	Input Capacitance	V <sub>IN</sub> = 0V	6 pF

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

**TABLE 7: RELIABILITY CHARACTERISTICS**

Symbol	Parameter	Minimum Specification	Units	Test Method
N <sub>END</sub> <sup>1</sup>	Endurance	10,000	Cycles	JEDEC Standard A117
T <sub>DR</sub> <sup>1</sup>	Data Retention	100	Years	JEDEC Standard A103
I <sub>LTH</sub> <sup>1</sup>	Latch Up	100 + I <sub>DD</sub>	mA	JEDEC Standard 78

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

**TABLE 8: AC OPERATING CHARACTERISTICS, V<sub>DD</sub> = 3.0-3.6V**

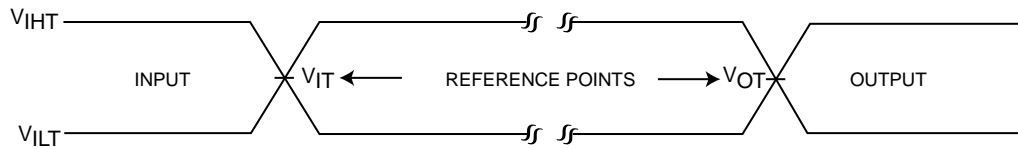
Symbol	Parameter	Limits		
		Min	Max	Units
F <sub>CLK</sub>	Serial Clock Frequency		10	MHz
T <sub>SCKH</sub>	Serial Clock High Time	45		ns
T <sub>SCKL</sub>	Serial Clock Low Time	45		ns
T <sub>CES</sub>	CE# Setup Time	250		ns
T <sub>CEH</sub>	CE# Hold Time	250		ns
T <sub>CPH</sub>	CE# High Time	250		ns
T <sub>CHZ</sub>	CE# High to High-Z Output		25	ns
T <sub>CLZ</sub>	SCK Low to Low-Z Output	0		ns
T <sub>RLZ</sub>	RST# Low to High-Z Output		25	ns
T <sub>DS</sub>	Data In Setup Time	20		ns
T <sub>DH</sub>	Data In Hold Time	20		ns
T <sub>OH</sub>	Output Hold from SCK Change	0		ns
T <sub>V</sub>	Output Valid from SCK		35	ns
T <sub>WPS</sub>	Write Protect Setup Time	10		ns
T <sub>WPH</sub>	Write Protect Hold Time	10		ns
T <sub>SE</sub>	Sector-Erase		25	ms
T <sub>SCE</sub>	Chip-Erase		100	ms
T <sub>BP</sub>	Byte-Program		20	µs
T <sub>RST</sub>	Reset Pulse Width	10		µs
T <sub>REC</sub>	Reset Recovery Time		1	µs
T <sub>PURST</sub>	Reset Time After Power-Up	10		µs

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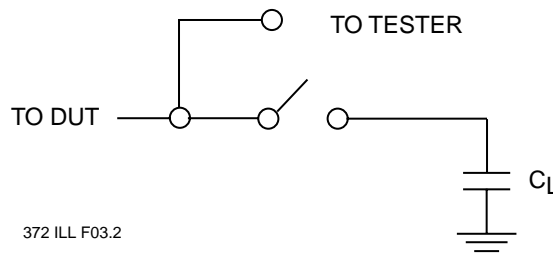


372 ILL F02.2

AC test inputs are driven at  $V_{IHT}$  ( $0.9 V_{DD}$ ) for a logic "1" and  $V_{ILT}$  ( $0.1 V_{DD}$ ) for a logic "0". Measurement reference points for inputs and outputs are  $V_{IT}$  ( $0.5 V_{DD}$ ) and  $V_{OT}$  ( $0.5 V_{DD}$ ). Input rise and fall times (10%  $\leftrightarrow$  90%) are  $<5$  ns.

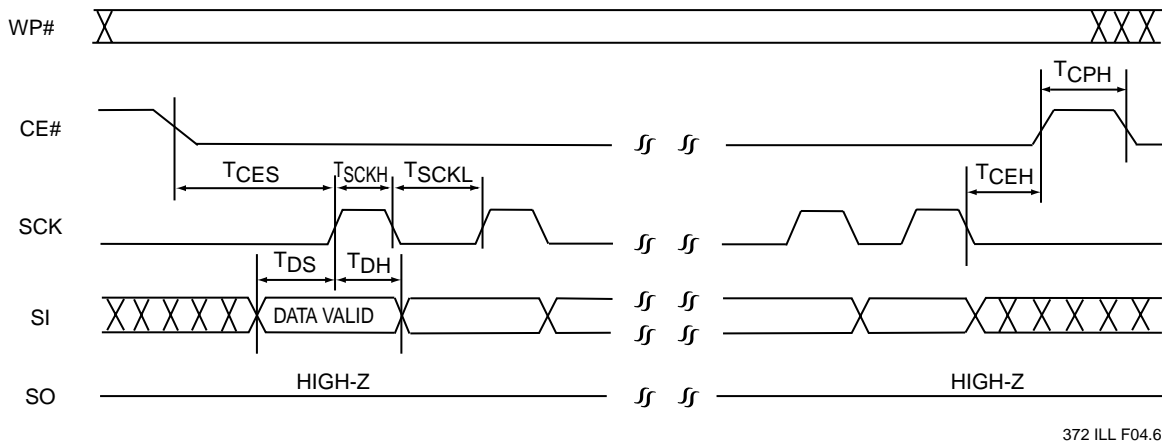
**Note:**  $V_{IT}$  -  $V_{INPUT}$  Test  
 $V_{OT}$  -  $V_{OUTPUT}$  Test  
 $V_{IHT}$  -  $V_{INPUT}$  HIGH Test  
 $V_{ILT}$  -  $V_{INPUT}$  LOW Test

FIGURE 2: AC INPUT/OUTPUT REFERENCE WAVEFORMS



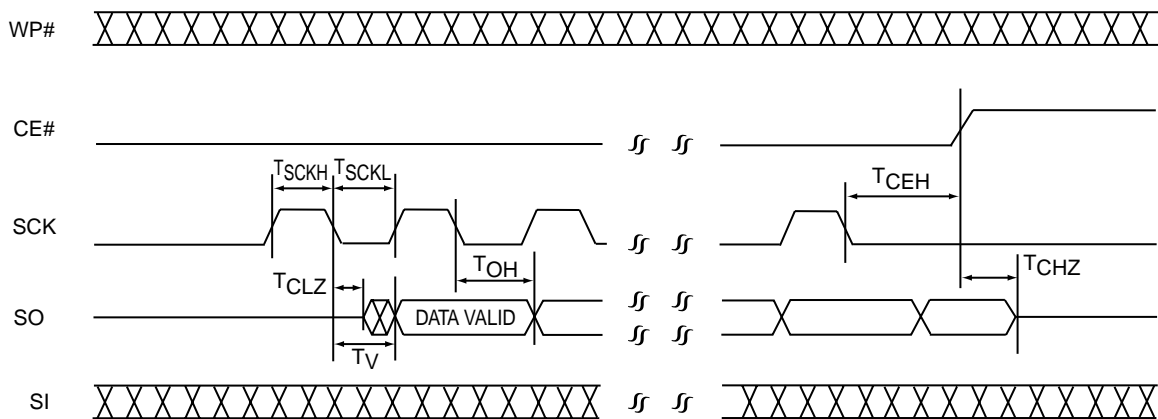
372 ILL F03.2

FIGURE 3: A TEST LOAD EXAMPLE



372 ILL F04.6

FIGURE 4: SERIAL INPUT TIMING DIAGRAM (INACTIVE SERIAL CLOCK LOW)



372 ILL F05.6

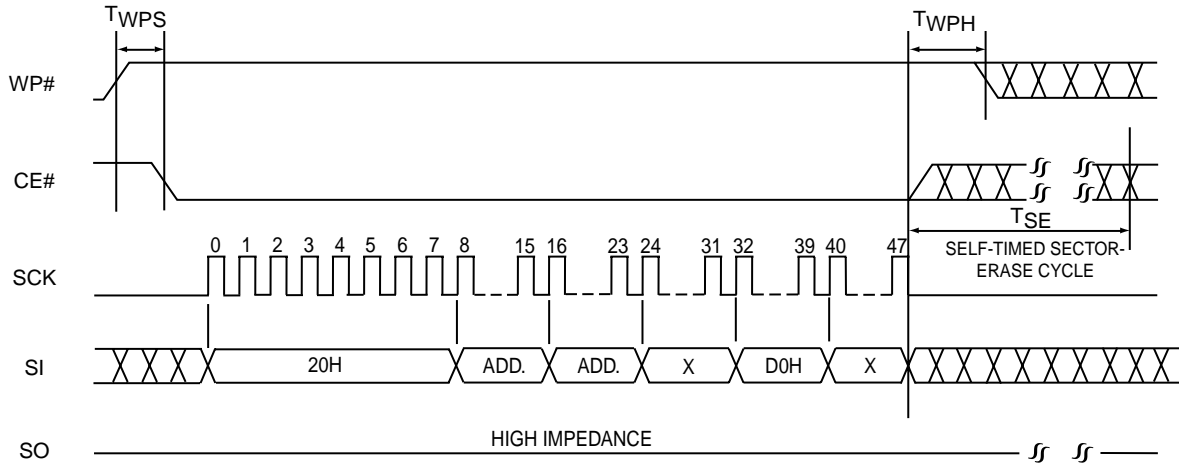
FIGURE 5: SERIAL OUTPUT TIMING DIAGRAM (INACTIVE SERIAL CLOCK LOW)





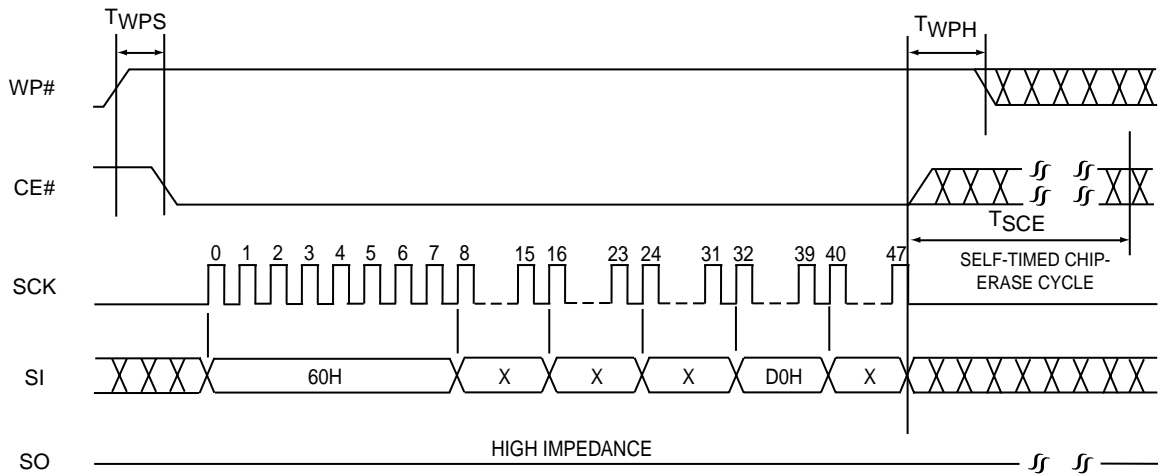
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372 ILL F06.7

FIGURE 6: SECTOR-ERASE TIMING DIAGRAM



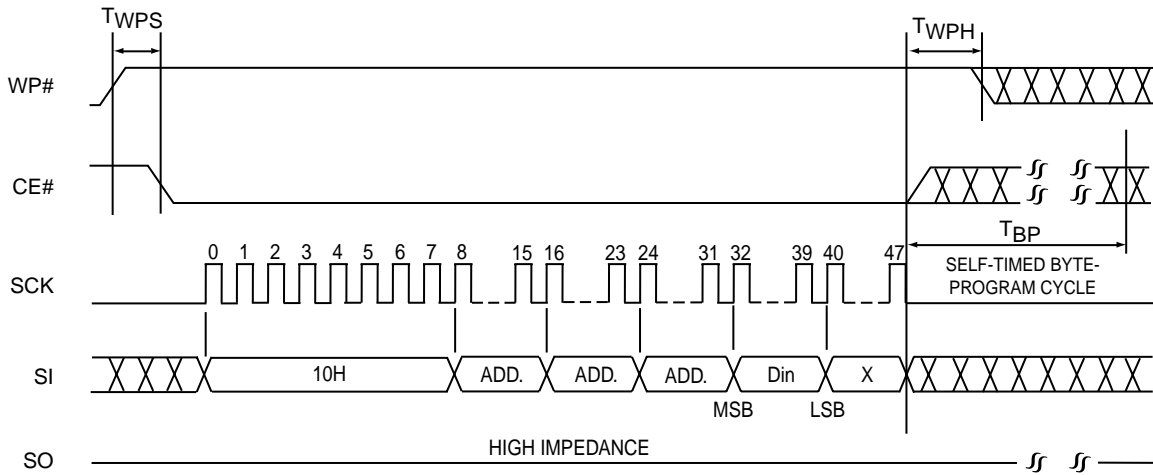
372 ILL F07.10

FIGURE 7: CHIP-ERASE TIMING DIAGRAM



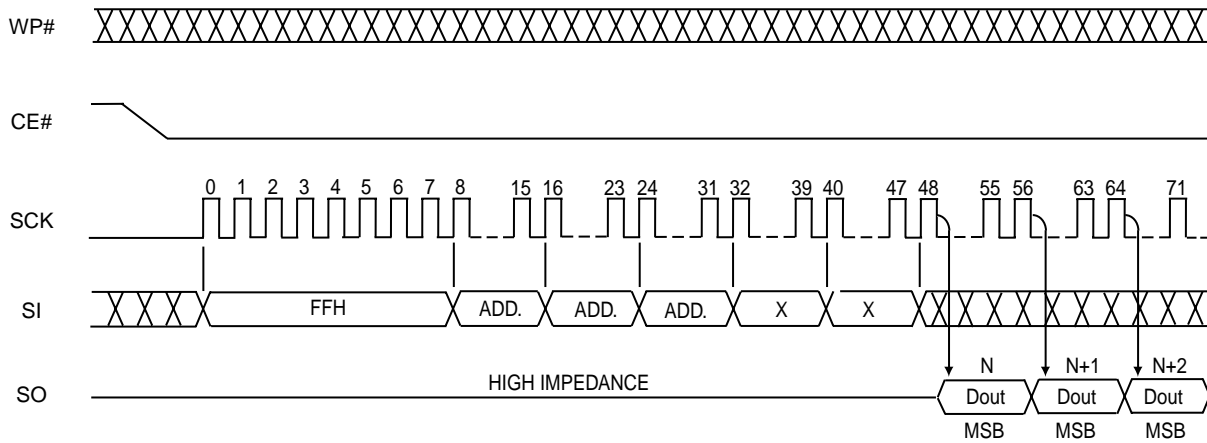
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**FIGURE 8: BYTE-PROGRAM TIMING DIAGRAM**



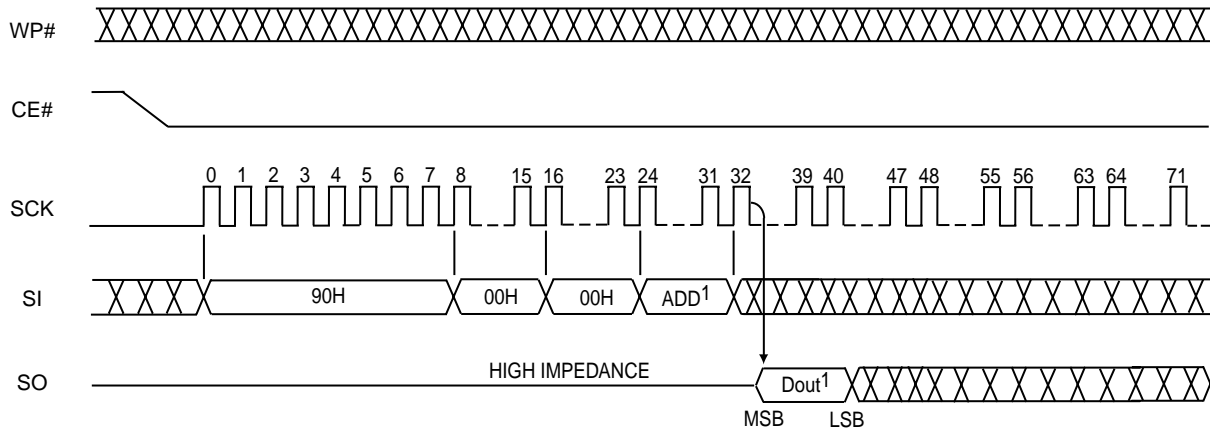
372 ILL F10.6

**FIGURE 9: READ TIMING DIAGRAM**



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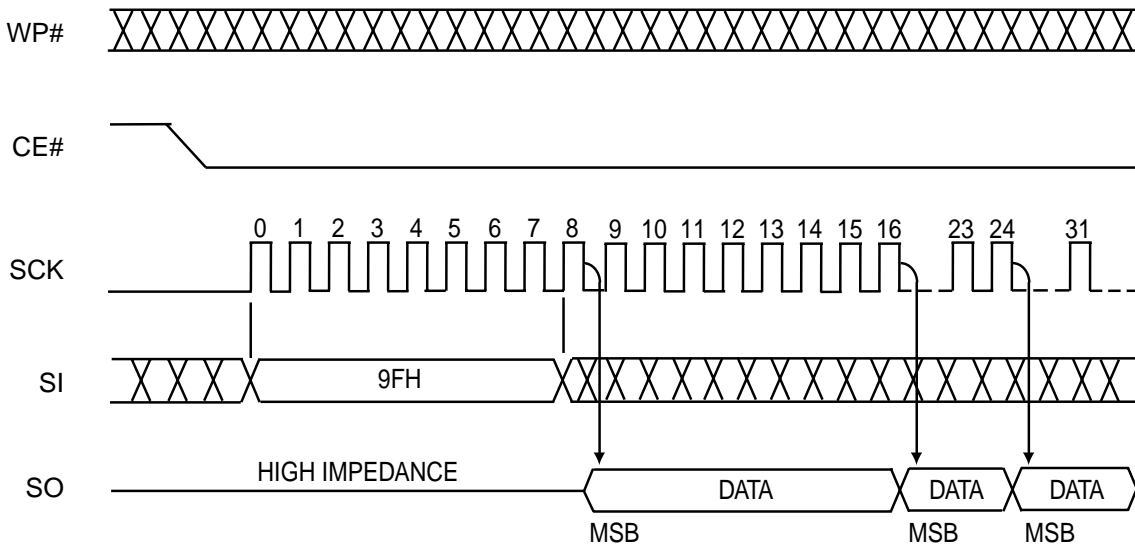
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Note: 1. SST Manufacturer's ID = BFH is read with  $A_0=0$   
SST45LF010 Device ID = 42H is read with  $A_0=1$

372 ILL F19.4

FIGURE 10: READ-ID TIMING DIAGRAM



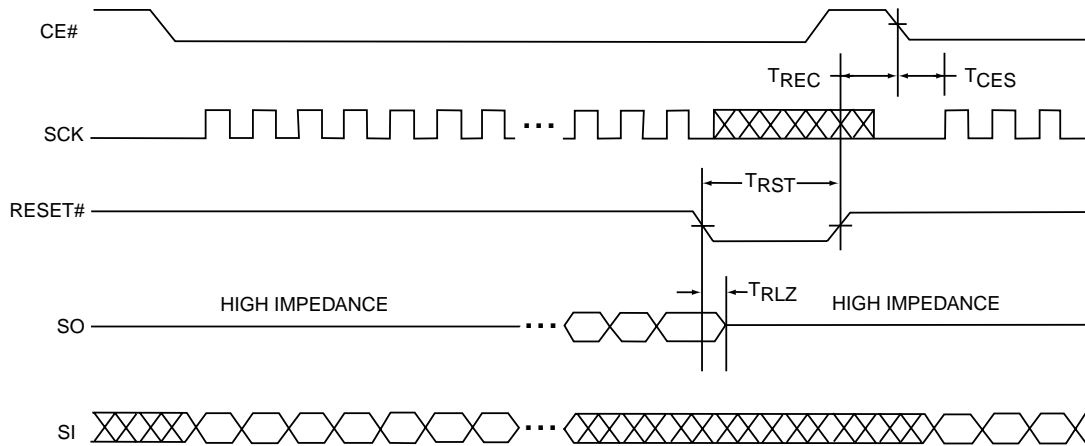
372 ILL F11.5

FIGURE 11: SOFTWARE-STATUS TIMING DIAGRAM



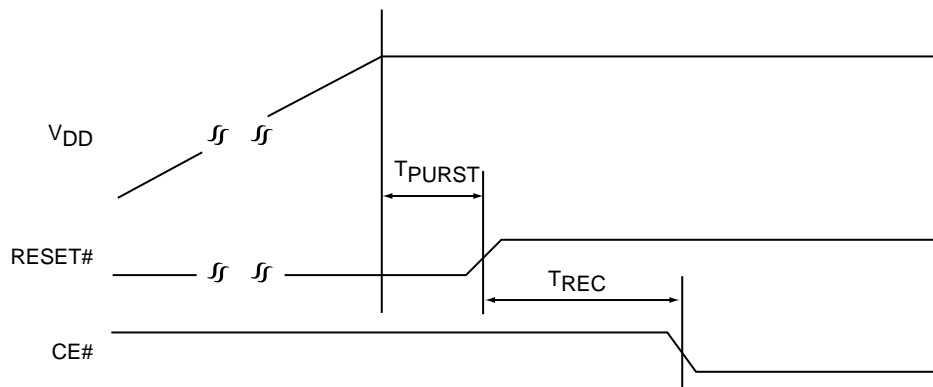
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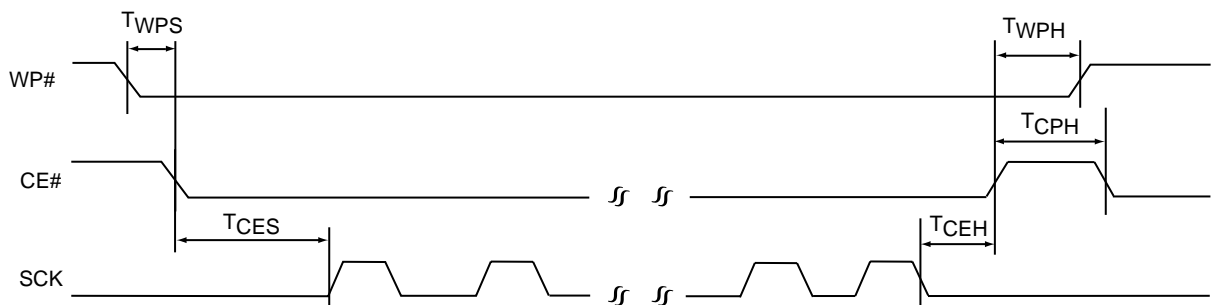
372 ILL F20.4

FIGURE 12: RESET TIMING DIAGRAM (INACTIVE CLOCK POLARITY LOW)



372 ILL F13.3

FIGURE 13: POWER-ON RESET TIMING DIAGRAM



372 ILL F14.1

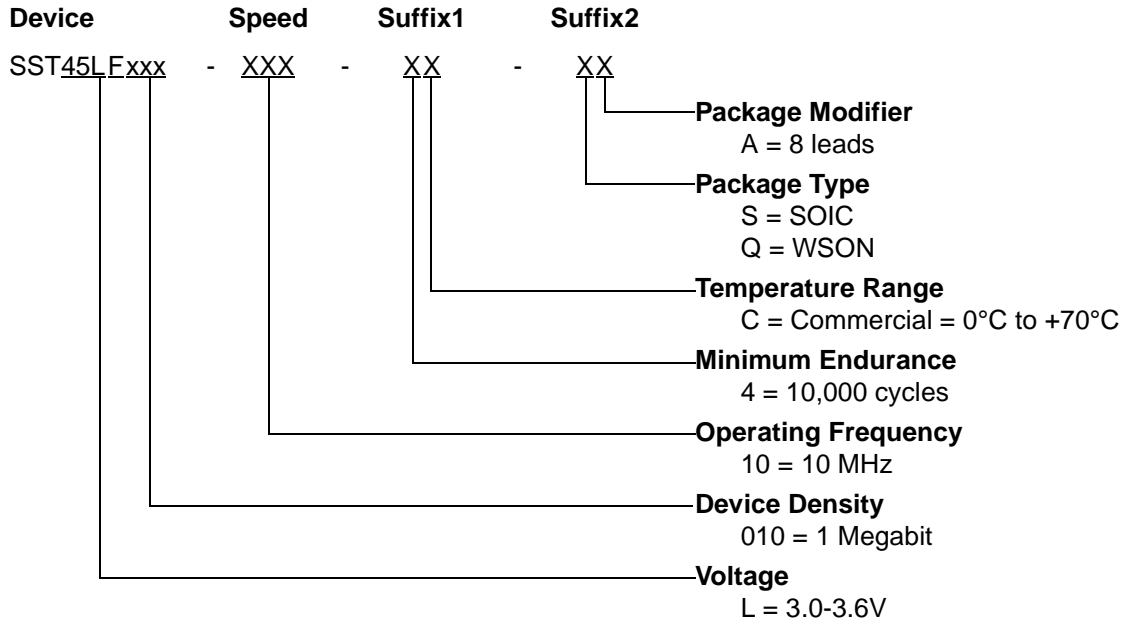
FIGURE 14: WRITE PROTECT TIMING DIAGRAM



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### SST45LF010 Valid combinations

SST45LF010-10-4C-SA    SST45LF010-10-4C-QA

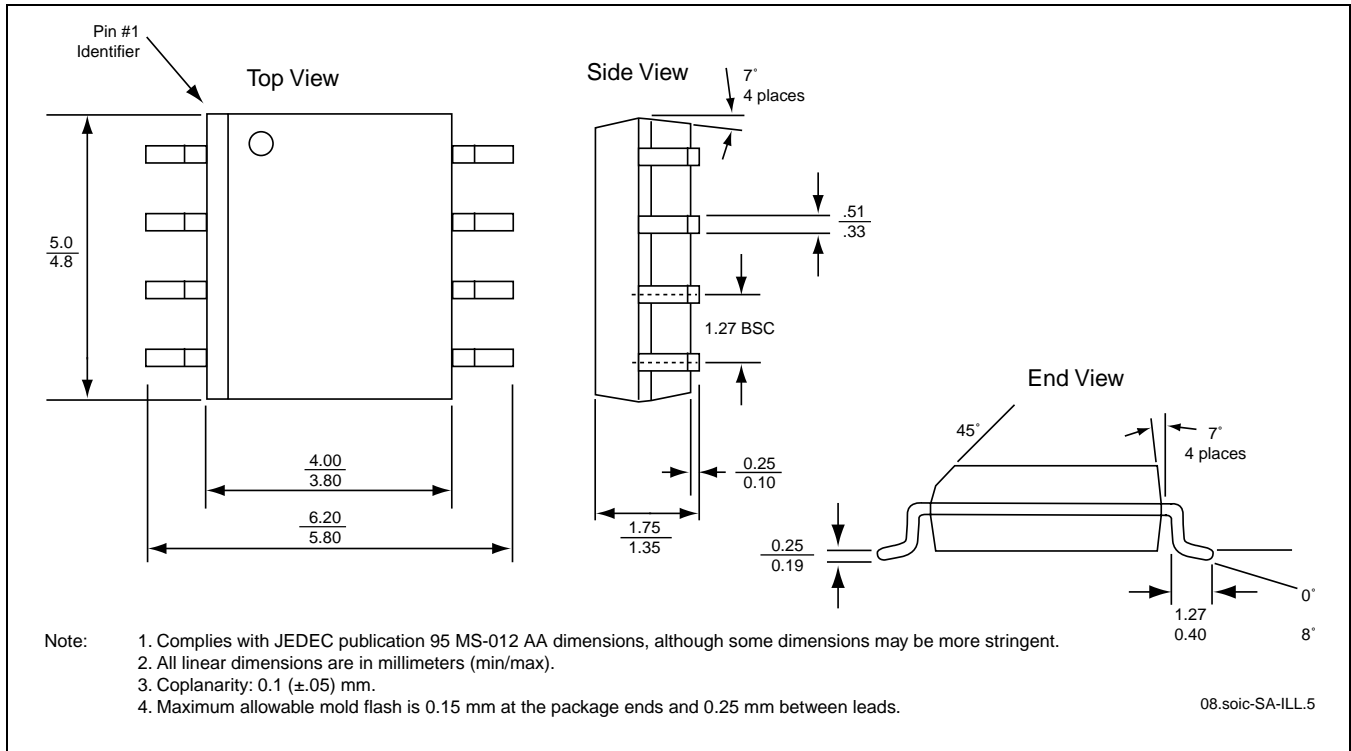
**Example:** Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.



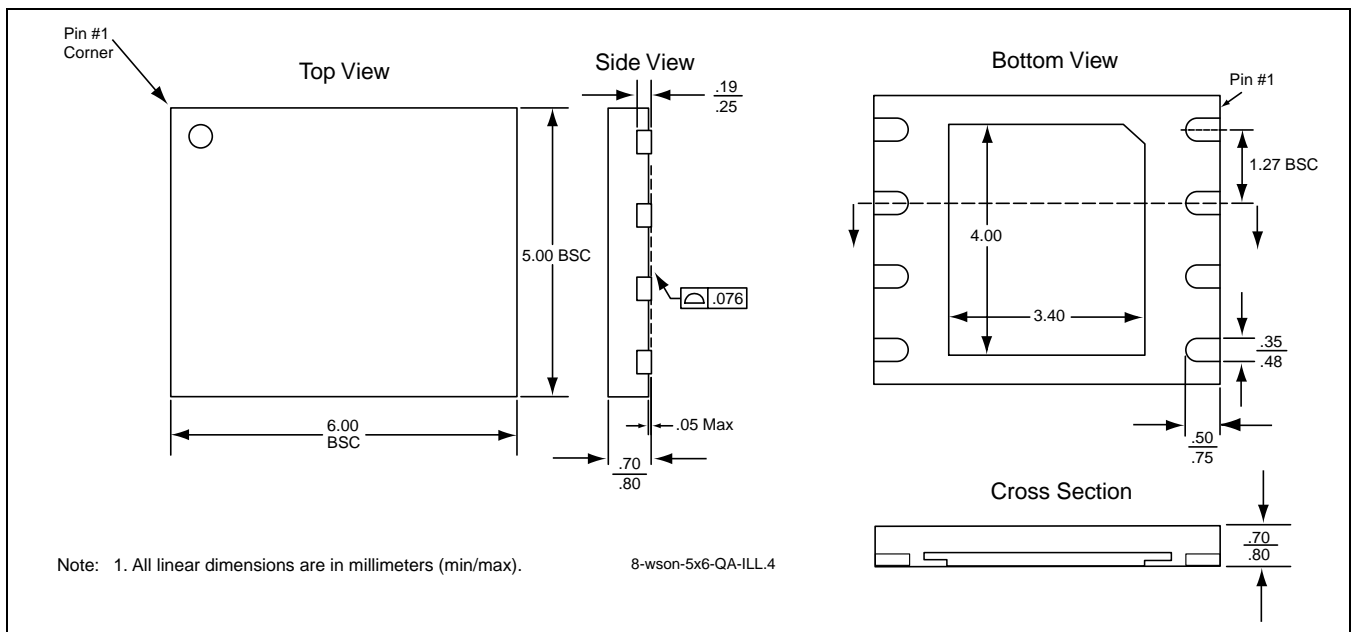
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## PACKAGING DIAGRAMS



### 8-LEAD SMALL OUTLINE INTEGRATED CIRCUIT PACKAGE (SOIC) SST PACKAGE CODE: SA



### 8-CONTACT ULTRA-THIN SMALL OUTLINE NO-LEAD PACKAGE (WSON) SST PACKAGE CODE: QA